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To cite this article: A Yu Kharin et al 2019 IOP Conf. Ser.: Mater. Sci. Eng. 475 012010

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Comparative analysis of silicon nanostructures by x-ray diffraction technique

A Yu Kharin¹, R B Assilbayeva², Yu V Kargina^{1,3} and V Yu Timoshenko^{1,3}

¹National Research Nuclear University "MEPhI", Bio-Nanophotonic Lab., 115409 Moscow, Russia

²Satpaev National Research Kazakh University, 050013 Almaty, Kazakhstan

³Lomonosov Moscow State University, Physics Department, 119991 Moscow, Russia

Corresponding author's e-mail address: AYKharin@mephi.ru

Abstract. Silicon nanoparticles and nanowires prepared by using different methods were investigated by means of x-ray diffraction (XRD) technique. Broadening of the XRD lines of crystalline Si lattice allows us to estimate the mean size of nanoparticles. Silicon nanoparticles stored in aqueous suspensions for several days were found to decrease their sizes due to dissolution process. The kinetics of dissolution for different kinds of nanoparticles were found to be different. It was also shown that the most unstable nanoparticles (microporous silicon ones) could be protected from dissolution via interaction with the polysaccharide molecules (dextrane) into the solution.

1. Introduction

Silicon (Si) nanostructures have attracted a lot of interest since the discovery of visible photoluminescence from porous silicon (PSi) [1]. PSi nanostructures have been considered for optoelectronics [2], photovoltaics [3,4], and various sensing [5,6] applications. Furthermore, it has been demonstrated a large panel of imaging and therapeutic modalities, including theranostic applications of PSi layer and Si nanoparticles (NPs) [7-9]. It was found that small Si NPs can be dissolved in water solution [10]. While the dissolution rate of bulk crystalline silicon (c-Si) is defined by the solution pH and orientation of the monocrystalline surface, the dissolution rate of NPs mainly depends on their size, morphology and surface oxide coating. Despite numerous different parameters, the most important dependence is that the small Si NPs are degraded into water solution during relatively short times (up to 24 h). The fact of fast degradation of Si NPs leads to arising from the huge number of research on the application of PSi NPs for drug delivery and controlled drug release [8]. Nevertheless, the control on the dissolution rate without changing the size of particles will be very helpful for the bio-applications of Si NPs. In the present paper, we show the possibility to monitor the mean size and dissolution rate of Si NPs by means of the XRD technique.

2. Materials and methods

Samples of microporous silicon were formed by the standard method of the electrochemical etching [1,2] of bulk c-Si wafers (p-type, boron doped to the specific resistance of 1-10 Ω^* cm, (100)oriented) in a mixture of hydrofluoric acid (48%) and ethanol (1:1). The time of etching was 40 min and the current density was 60 mA/cm². The free standing PSi films were obtained by lifting from the substrate after applying a short pulse of the etching current 500 mA/cm². Prior investigations the porous silicon films were air-dried for one week. The mesoporous silicon was obtained using the

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similar procedure on a heavily boron-doped p-type silicon wafer, with the specific resistivity of 1-5 m Ω^* cm, (100)-oriented. Silicon nanowires (SiNWs) were obtained by using metal-assisted chemical etching of c-Si wafers of p-type, boron doped, 1-10 Ω^* cm, (100)-oriented (see for details Refs. [11,12]. In order to investigate the stability of Si nanostructures in water, the corresponding powders were suspended in water. Microporous silicon (12 mg) was ground in the presence of water (1 mL) or an aqueous solution of dextrane. Powders of Si NPs prepared by microwave induced decomposition of SiH₄ [13] were also studied.

XRD spectra were measured using a RENOM apparatus (EXPERTCENTER Ltd., Russia) with Cu K α line (λ =0.154184 nm) at room temperature in air. Measurements were done for powders just after synthesis, after mixing with water or aqueous dextrane solution followed by drying in air.

3. Results and discussion

Figure 1 shows typical XRD patterns for c-Si powder, SiNWs, meso- and micro- PSi in semilogarithmic scale. It can be clearly seen that there is almost no difference in XRD patterns of c-Si and Si NWs within the detection limit 0.01 deg. The XRD spectrum of SiNWs consists of peaks corresponding to the presence of silver (Ag) nanoparticles used during the synthesis. The amount of silver, estimated via the corundum numbers is 2 ± 0.5 mass %. The amount of amorphous phase corresponds to the background signal intensities, so the relative amount of amorphous oxide can be measured as a ratio between background signal and peak intensity.

Mean size of Si nanocrystals in micro- and meso-PSi can be estimated from the broadening of diffraction line by using the Scherrer equation:

$$d = \frac{\kappa_{\lambda}}{\Delta \theta \cos \theta} , \qquad (1)$$

where λ is the wavelength of x-ray radiation (λ =0.154184 nm, in our case), K is a dimensionless shape factor close to unity, $\Delta\theta$ is the line broadening at half the maximum intensity (FWHM), θ is the Bragg angle of the corresponding crystallographic plane.

According to Eq.1 the mean size of Si crystallites in micro-PSi and meso-PSi is 2.7-4.4 nm and 10-15 nm, respectively, which in accordance with the literature data for similar preparation conditions [1,2].

Figure 2 shows XRD spectra for Si NPs prepared by silane decomposition and c-Si powder (for comparison). The broadening of Si NPs lines allows us to estimate the nanocrystal mean sizes to be about 30-40 nm. The background of XRD spectrum of Si NPs indicates the presence of amorphous phases, which can be both amorphous Si and SiO₂.



Figure 1. XRD spectra of powders of c-Si, SiNWs, meso-PSi and micro-PSi. Black squares and red triangles indicate positions of the corresponding scattering angles for c-Si and crystalline silver from the XRD database.

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Figure 2. XRD spectra of powders of Si NPs prepared by silane decomposition and c-Si (for comparison).

According to Figure 3, the storage of Si NWs in water did not significantly change the XRD patterns, while the grinding of porous silicon in the presence of water during 10 min cause a significant change of XRD. It is known that micro-PSi can be oxidized by water [2], so the silicon peaks disappear. Instead of it, we can see an increase in the background caused by the presence of amorphous silicon oxide.



Figure 3. XRD spectra of Si NWs before and after storage in water for a different time.

Assuming that the average thickness of oxide layer at the surface of silicon at room temperature without thermal treatment usually varies from 1 to 1.5 nm and taking into account the shape and size of the particles we can calculate the ratio between Si and SiO₂ phases. It can be expressed through the bond absorption for each type of particles. The ratio of background intensity (caused mainly by the presence of amorphous SiO₂) and integral intensity of XRD silicon peak with a maximum at 28.44^o can be used to show the increasing amount of amorphous silica in nanostructures with a decrease of their size. It allows us to propose the following expression for the ratio between XRD intensities and masses of Si and SiO₂ fractions:

$$\frac{I_{background}}{I_{peak}} \sim \frac{m_{SiO2}}{m_{Si}}$$
 (2)

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Figure 4 shows the data calculated according to Eq.2 versus the mean size of Si nanocrystals.

Figure 4. Dependence of the ratio between the XRD background and intensities of the characteristic c-Si lines vs. mean size of Si nanocrystals.

Figure 4 shows that the decrease of the size of Si nanocrystals results in an increase of the content of silica phase. Nevertheless, in the case of relatively big nanostructures, the oxidation layer seems to correspond the model of constant silica thickness, while in the case of porous silicon we can see that the particles are much less oxidized than they are supposed to be from the model of free-standing crystallites. That effect is probably caused by the complicated porous structure of the nanoparticles. That structure slows down the diffusion of oxygen. That effect also leads to the possibility of self-inflammation or even explosion of porous silicon during mechanical treatment. After grinding of PSi layer in water, we can observe the partial oxidation of the microporous silicon (green triangle in Fig.4) and formation of silicon oxide in amount equivalent to the formation of 1nm layer of silicon dioxide on each crystallite.



Figure 5. (a) XRD spectra of micro-PSi before and after grinding in water: (b) the same spectra for micro-PSi treated in an aqueous solution of dextrane.

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One of the ways to protect Si NPs from rapid degradation in water is based on the coating of the NPs with polymer shell [13]. We used the grinding of PSi in dextrane solution in order to evaluate if the simple presence of this polymer has the protective effect. Figure 5 shows XRD spectra of porous silicon before and after grinding into the dextrane solution. It can be easily seen that there is no noticeable difference between XRD patterns. This fact is explained by the protective role of dextrane for Si nanocrystal surfaces.

4. Conclusion

We show that the XRD method, which is usually rarely used for silicon nanostructures, have great potential for the determination of the size of nanocrystals, the amount of silicon oxide (after calibration) and it can be used to monitor the stability/degradation of silicon nanostructures in aqueous solutions. The XRD measurements demonstrated a correlation between the silicon nanocrystal size and the content of the amorphous silica in different nanostructures. It was shown, that the fast oxidation of small silicon particles takes place in water, but it was shown that it could be slowed down by the dextrane coating of the particles. The obtained results can be useful for the control of biodegradation in the case of bioapplications of silicon nanoparticles.

Acknowledgments

Authors (V.Yu.T. and K.Yu.V.) acknowledge the financial support of the Russian Foundation for Basic Research (grant 16-02-00668) and R.B.A. thanks the Ph.D. Program of Satpaev National Research Kazakh University.

References

- [1] Canham L T 1990 *Appl. Phys. Lett.* **57(10)** 1046
- [2] Sailor M J 2012 Porous silicon in practice: preparation, characterization and applications (Weinheim: Germany) 254
- [3] Wu C, Crouch C H, Zhao L et al 2001 *Appl.Phys. Lett.* **78(13)** 1850
- [4] Halbwax M, Sarnet T, Delaporte P et al 2008 Thin solid films 516(20) 6791
- [5] Lin V S Y, Motesharei K, Dancil K P S et al 1997 Science 278(5339) 840
- [6] Konstantinova E A, Ryabchikov Y V, Osminkina L A et al 2004 Semicond. 38(11) 1344
- [7] Erogbogbo F, Yong K T, Roy I, Xu G, Prasad P N, Swihart M T 2008 ACS Nano 2(5) 873
- [8] Park J H, Gu L, Von Maltzahn G, Ruoslahti E et al 2009 Nat. Mat. 8(4) 331
- [9] Kabashin A V, Timoshenko V Yu 2016 Nanomedicine 11(17) 2247
- [10] Canham L T 2007 Nanotechnology 18(18) 185704
- [11] Osminkina L A, Sivakov V A, Mysov G Aet al 2014 NRL 9(1) 1
- [12] Timoshenko V Y, Gonchar K A, Golovan L A et al 2011 J. Nan. and Opt. 6(4) 519
- [13] Gongalsky M B, Kharin A Y, Osminkina L A et al 2012 NRL 7(1) 1